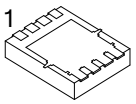
USG130N10 **Advance** ***POWER MOSFET***

130A, 100V N-CHANNEL ENHANCEMENT MODE TRENCH POWER MOSFET



DFN5060-8

■ DESCRIPTION

The UTC **USG130N10** is a N-channel Power MOSFET, it uses UTC's advanced technology to provide the customers with low $R_{DS(ON)}$ characteristic by high cell density trench technology.

The UTC **USG130N10** is suitable for high efficiency synchronous rectification in SMPS, UPS, hard switched and high frequency circuits.

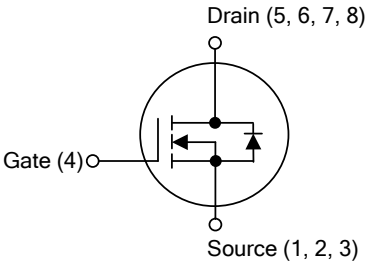
■ APPLICATION

* Synchronous Rectification in SMPS
* Hard Switching and High Speed Circuit
* DC/DCin Telecoms and Inductrial

■ FEATURES

* $R_{DS(ON)}$ ≤ 4.2 mΩ @ V_{GS}=10V, I_D=20A
  $R_{DS(ON)}$ ≤ 6.0 mΩ @ V_{GS}=4.5V, I_D=20A
* Optimized for high speed switching, Logic level
* Enhanced Body diode dv/dt capability
* Enhanced Avalanche Ruggedness

■ SYMBOL



■ ORDERING INFORMATION

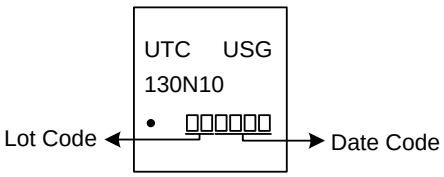
Ordering Number		Package	Pin Assignment								Packing
Lead Free	Halogen Free		1	2	3	4	5	6	7	8	
USG130N10L-K08-5060-R	USG130N10G-K08-5060-R	DFN5060-8	S	S	S	G	D	D	D	D	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

USG130N10G-K08-5060-R

(1)Packing Type	(1) R: Tape Reel
(2)Package Type	(2) K08-5060: DFN5060-8
(3)Green Package	(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	100	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current	Continuous	I_D	130	A
Pulsed Drain Current	Pulsed (Note 2)	I_{DM}	400	A
Avalanche energy	Single Pulsed (Note 3)	E_{AS}	180	mJ
Power Dissipation		P_D	41	W
Junction Temperature		T_J	+150	°C
Storage Temperature Range		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. L=0.1mH, I_{AS}=60A, V_{DD}=50V, R_G=25Ω, Starting T_J = 25°C.

■ THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient (Note)	θ_{JA}	35	°C/W
Junction to Case	θ_{JC}	3	°C/W

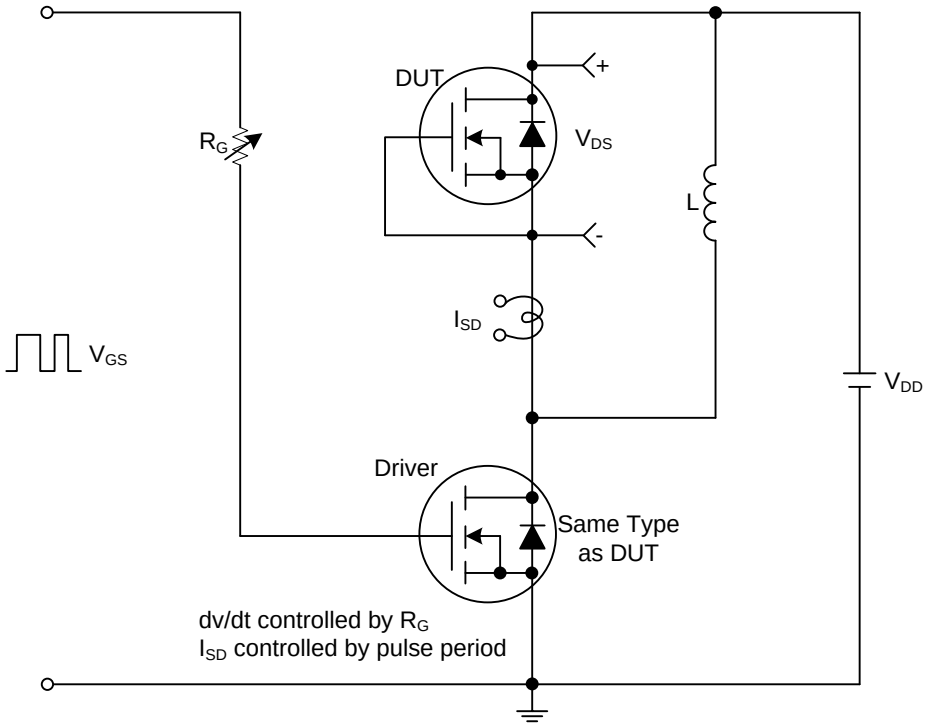
Note: Device mounted on FR-4 substrate P_C board, 2oz copper, with 1inch square copper plate.

■ ELECTRICAL CHARACTERISTICS (T_J =25°C, unless otherwise specified)

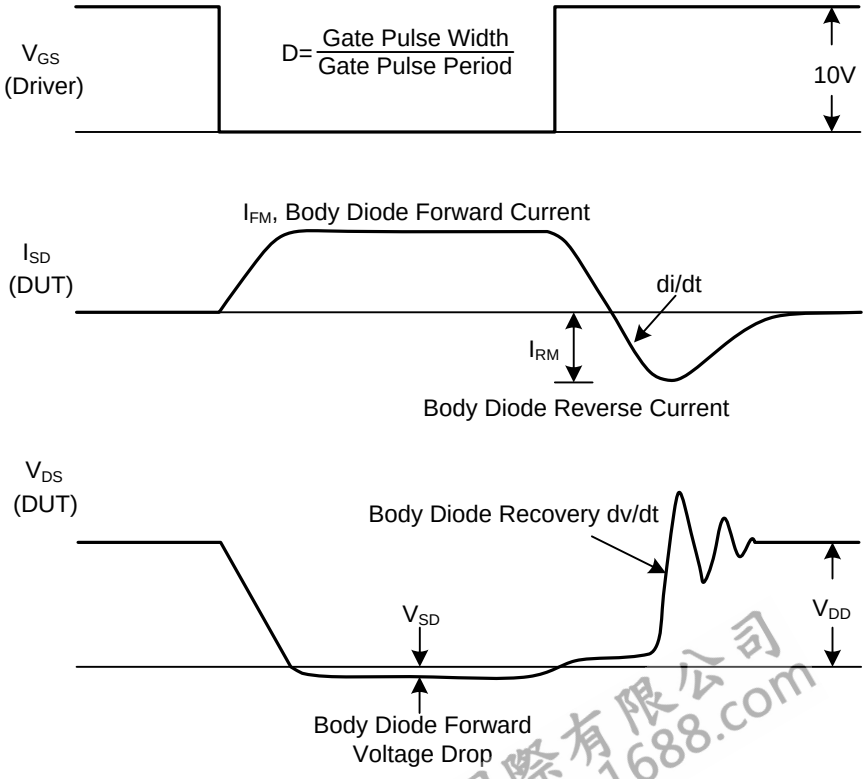
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	I_D=250μA, V_{GS}=0V	100			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=60V, V_{GS}=0V			1	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{GS}=+20V, V_{DS}=0V			+100	nA
	Reverse		V_{GS}=-20V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	1.4	1.8	2.4	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=20A		3.4	4.2	mΩ
			V_{GS}=4.5V, I_D=20A		4.6	6.0	mΩ
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I_S				130	A
Maximum Body-Diode Pulsed Current		I_{SM}				400	A
Drain-Source Diode Forward Voltage (Note 1)		V_{SD}	I_F=20A, V_{GS}=0V		0.9	1.2	V

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle≤2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS



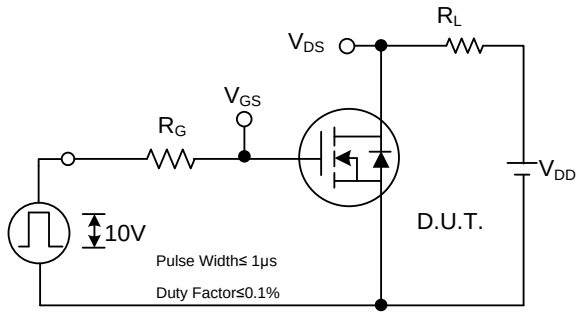
Peak Diode Recovery dv/dt Test Circuit



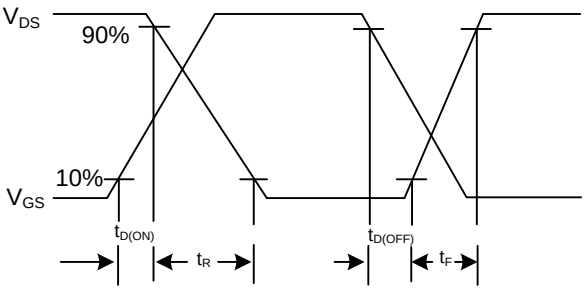
Peak Diode Recovery dv/dt Test Circuit and Waveforms

Peak Diode Recovery dv/dt Waveforms

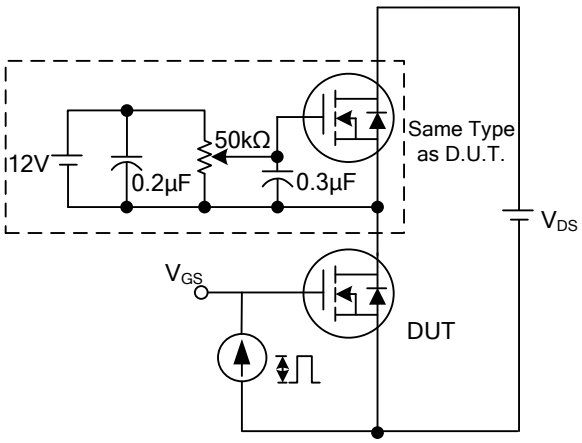
■ TEST CIRCUITS AND WAVEFORMS



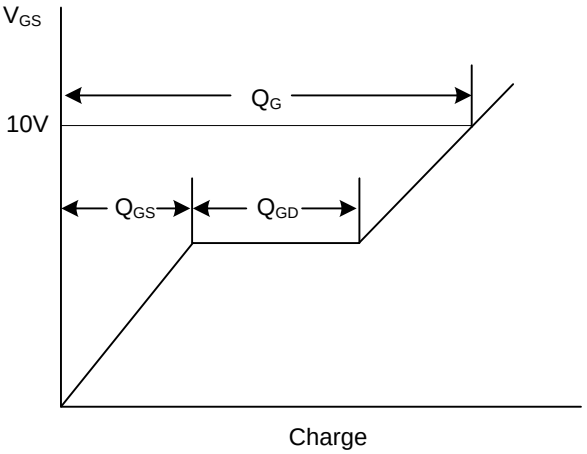
Switching Test Circuit



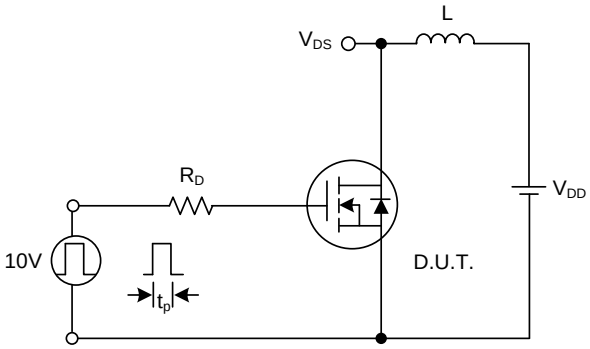
Switching Waveforms



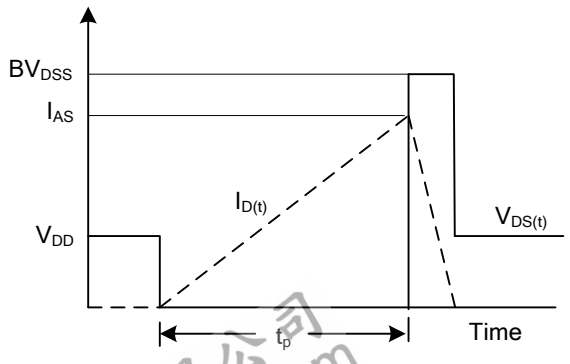
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms